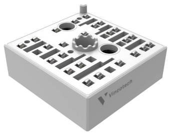
MiniSKiiP® 1 PIM | **1200 V / 15 A**

Features

- Solderless interconnection
- Trench Fieldstop IGBT4 technology

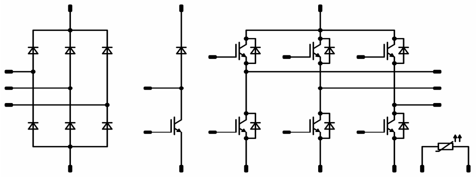
MiniSKiiP® 1 housing



Target Applications

- Industrial drives

Schematic



Types

- V23990-K200-A40-PM

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Rectifier Diode				
Repetitive peak reverse voltage	V_{RRM}		1600	V
DC forward current	I_{FAV}		25	A
Surge (non-repetitive) forward current	I_{FSM}	t_p = 10 ms half sine	220	A
I^2t-value	I^2t	t_p = 10 ms half sine	200	A^2s
Power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	51	W
Maximum Junction Temperature	T_{jmax}		150	°C
Inverter Switch / Brake Switch				
Collector-emitter breakdown voltage	V_{CE}		1200	V
DC collector current	I_C		15	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	45	A
Power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	88	W
Gate-emitter peak voltage	V_{GE}		±20	V
Short circuit ratings	t_{SC}	$T_j \le$ 150 °C V_{GE} = 15 V , V_{CC} = 800 V	10	μs
Maximum Junction Temperature	T_{jmax}		175	°C
Inverter Diode / Brake Diode				
Repetitive peak reverse voltage	V_{RRM}		1200	V
DC forward current	I_F		15	A
Power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	66	W
Maximum Junction Temperature	T_{jmax}		175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{op}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{is}	t = 2 s	DC Test Voltage*	5500	V
		t = 1 min	AC Voltage	2500	V
Creepage distance		With std lid For more information see handling instructions		6,3	mm
Clearance		With std lid For more information see handling instructions		6,3	mm
Comparative Tracking Index	CTI			>200	

* 100 % tested in production

Characteristic Values

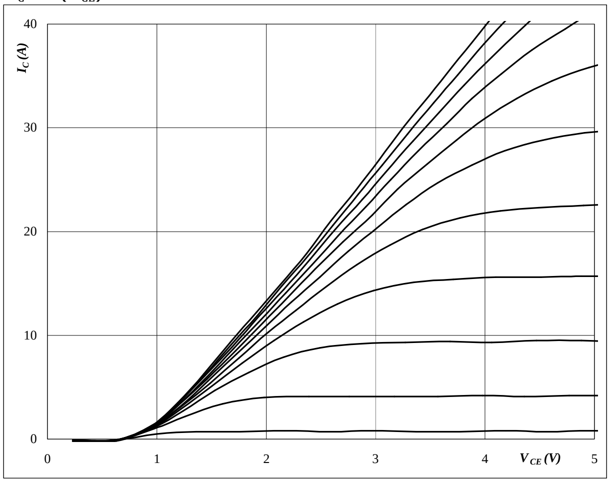
Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_r [V] V_{CE} [V] V_{DS} [V]	I_C [A] I_F [A] I_D [A]	T_j [°C]	Min	Typ	Max	Unit
Rectifier Diode										
Forward voltage	V_F				25	25 125		1,51 1,42		V
Threshold voltage (for power loss calc. only)	V_{to}				25	25 125		0,86 0,79		V
Slope resistance (for power loss calc. only)	r_t				25	25 125		0,03 0,03		Ω
Reverse current	I_r			1500		25			0,05	mA
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 2,5 W/mK (HPTP)						1,37		K/W
Inverter Switch / Brake Switch										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0005	25	5,3	5,8	6,3	V
Collector-emitter saturation voltage	V_{CEsat}		15		15	25 150	1,6	2,2 2,48	2,4	V
Collector-emitter cut-off current incl. Diode	I_{CES}		0	1200		25			0,06	mA
Gate-emitter leakage current	I_{GES}		20	0		25			180	nA
Integrated Gate resistor	R_{gint}							none		Ω
Turn-on delay time	$t_{d(on)}$	R_{goff} = 32 Ω R_{gon} = 32 Ω	±15	600	15	25 150		102 102		ns
Rise time	t_r					25 150		33 37		
Turn-off delay time	$t_{d(off)}$					25 150		216 284		
Fall time	t_f					25 150		90 133		
Turn-on energy loss	E_{on}					25 150		0,99 1,53		mWs
Turn-off energy loss	E_{off}					25 150		0,9 1,47		
Input capacitance	C_{ies}	f = 1 MHz	0	25		25		890		pF
Reverse transfer capacitance	C_{rss}							30		
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 2,5 W/mK (HPTP)						1,08		K/W
Inverter Diode / Brake Diode										
Diode forward voltage	V_F				15	25 150	1,6	2,6 2,64	2,9	V
Peak reverse recovery current	I_{RRM}	R_{goff} = 32 Ω	±15	600	15	25 150		7,78 10,8		A
Reverse recovery time	t_{rr}					25 150		299 541		ns
Reverse recovered charge	Q_{rr}					25 150		0,98 2,33		µC
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 150		73 47		A/µs
Reverse recovered energy	E_{rec}					25 150		0,38 0,97		mWs
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 2,5 W/mK (HPTP)						1,44		K/W
Thermistor										
Rated resistance	R					25		1000		Ω
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1670 Ω				100	-2		2	%
R_{100}	R					100		1670		Ω
Power dissipation constant						25		0,76		mW/K
A-value	$B_{(25/50)}$					25		$7{,}635 \cdot 10^{-3}$		1/K
B-value	$B_{(25/100)}$					25		$1{,}731 \cdot 10^{-5}$		1/K²
Vincotech NTC Reference									E	

Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 1.	IGBT

Typical output characteristics

$I_C = f(V_{CE})$



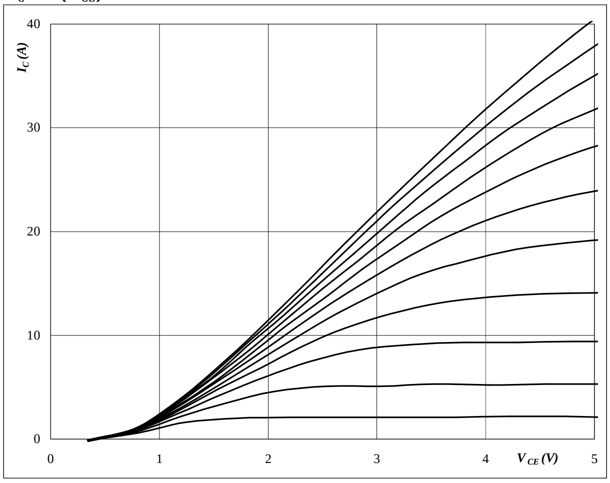
At

t_p =	250	μs
T_j =	25	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

figure 2.	IGBT

Typical output characteristics

$I_C = f(V_{CE})$



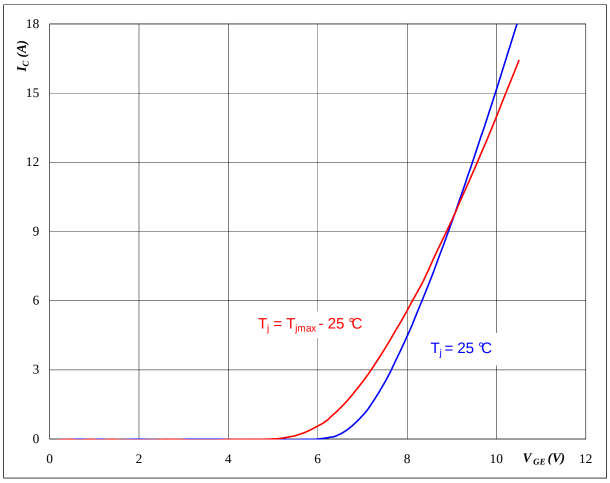
At

t_p =	250	μs
T_j =	150	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

figure 3.	IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$



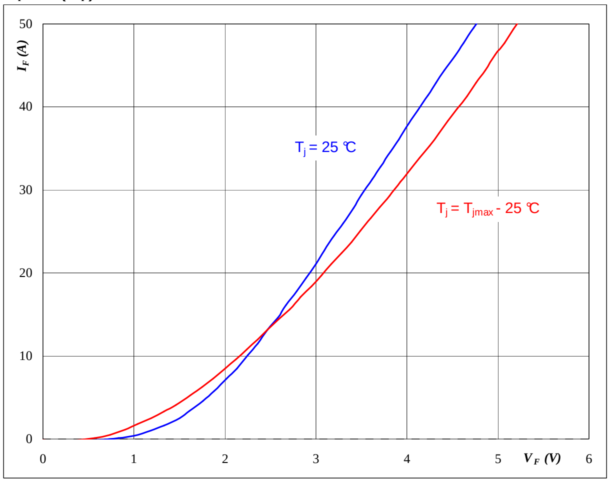
At

t_p =	250	μs
V_{CE} =	10	V

figure 4.	FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

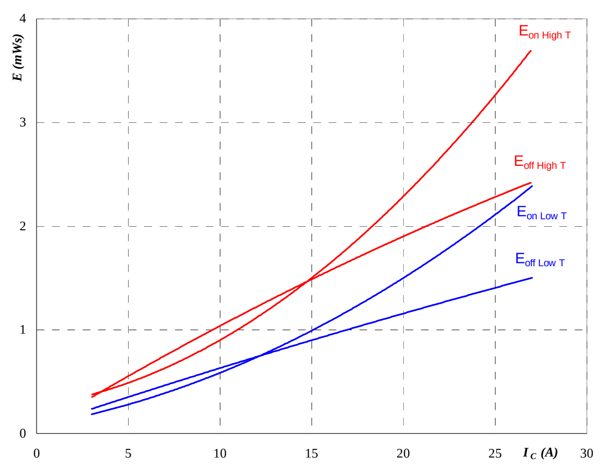
t_p =	250	μs

Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 5. **IGBT**

Typical switching energy losses
as a function of collector current

$E = f(I_C)$



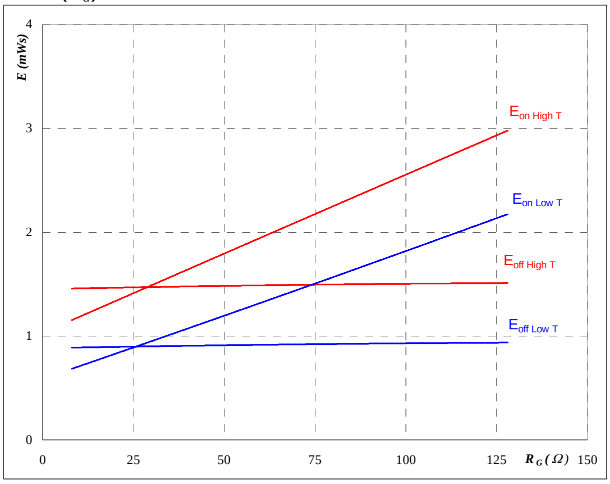
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω
R_{goff} =	32	Ω

figure 6. **IGBT**

Typical switching energy losses
as a function of gate resistor

$E = f(R_G)$



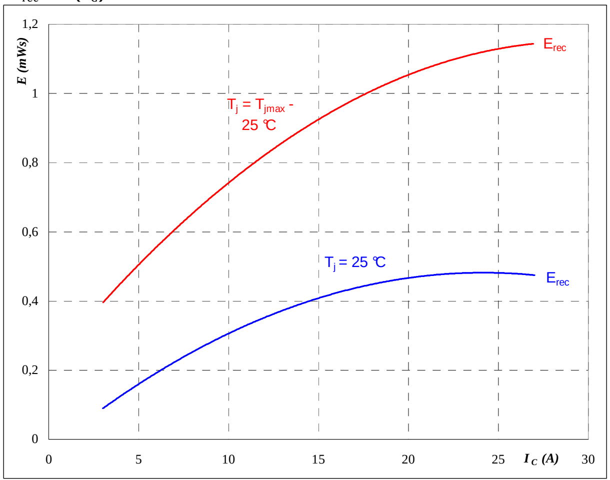
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

figure 7. **FWD**

Typical reverse recovery energy loss
as a function of collector current

$E_{rec} = f(I_C)$



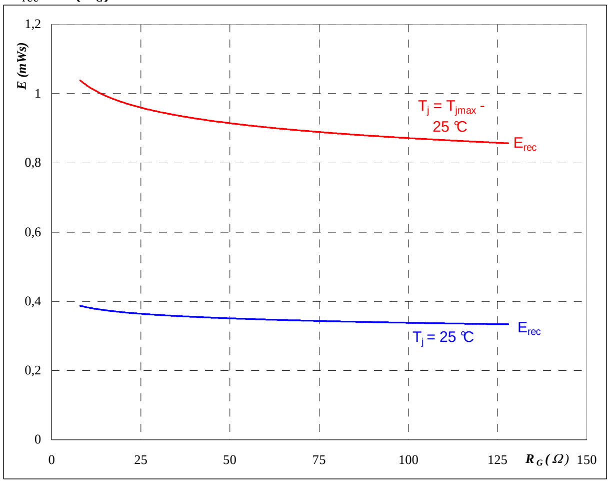
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

figure 8. **IGBT**

Typical reverse recovery energy loss
as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

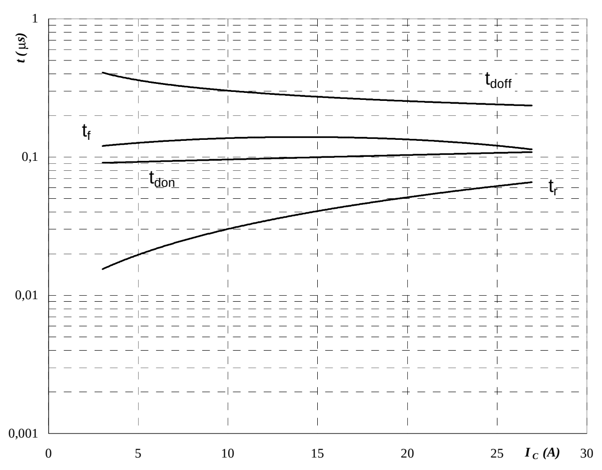
T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 9. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



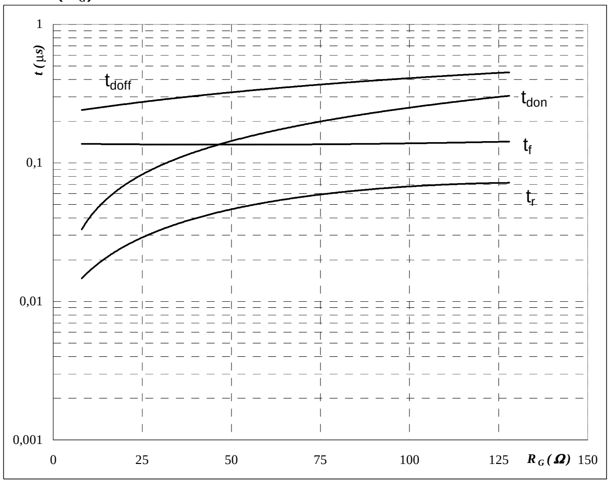
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω
R_{goff} =	32	Ω

figure 10. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_G)$



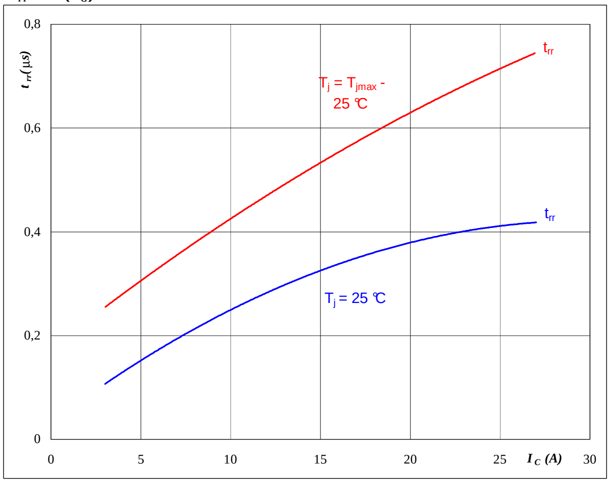
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	15	A

figure 11. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



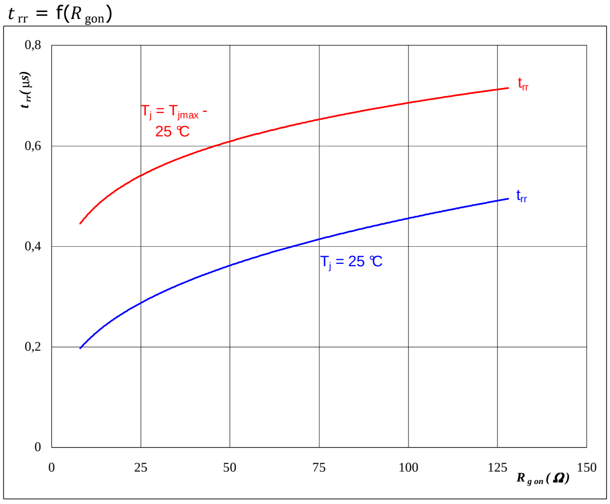
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

figure 12. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



At

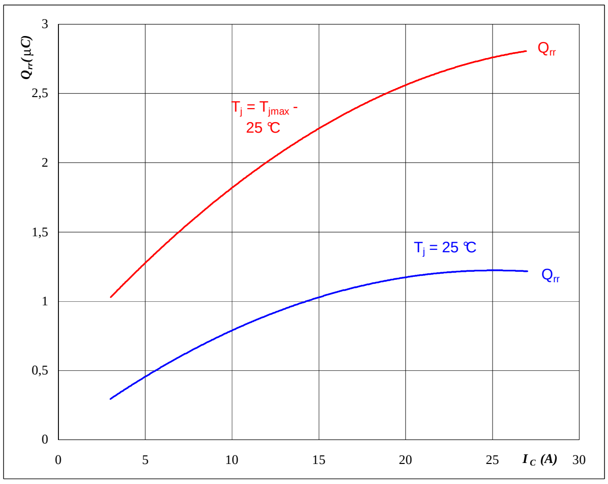
T_j =	25/150	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 13. **FWD**

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



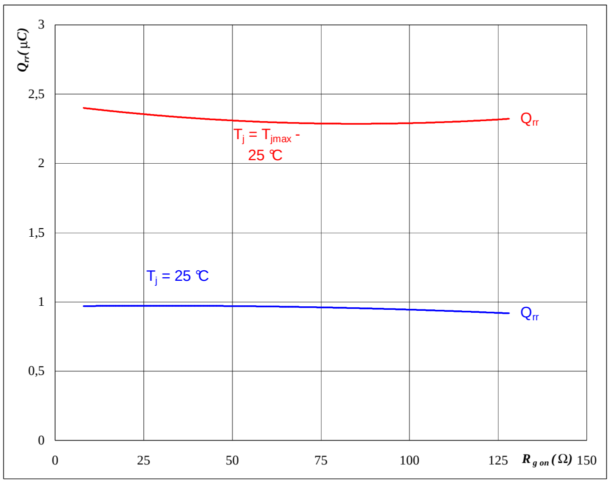
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

figure 14. **FWD**

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



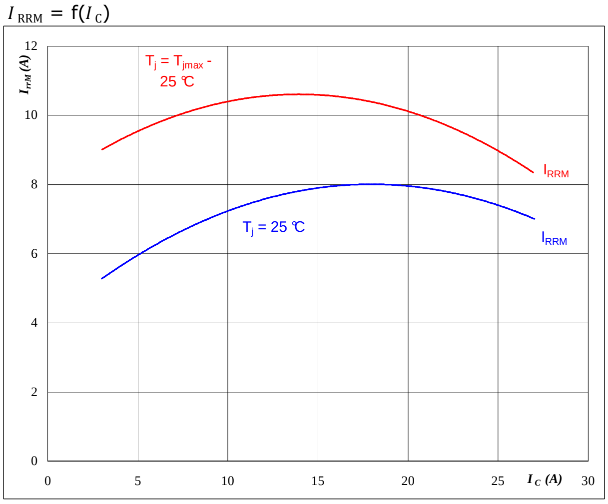
At

T_j =	25/150	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

figure 15. **FWD**

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



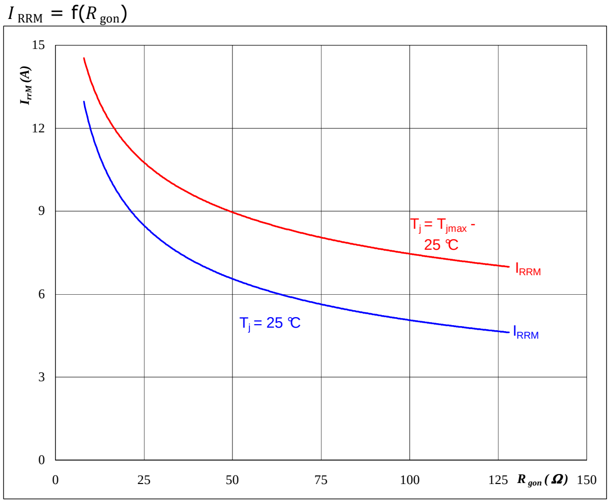
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

figure 16. **FWD**

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

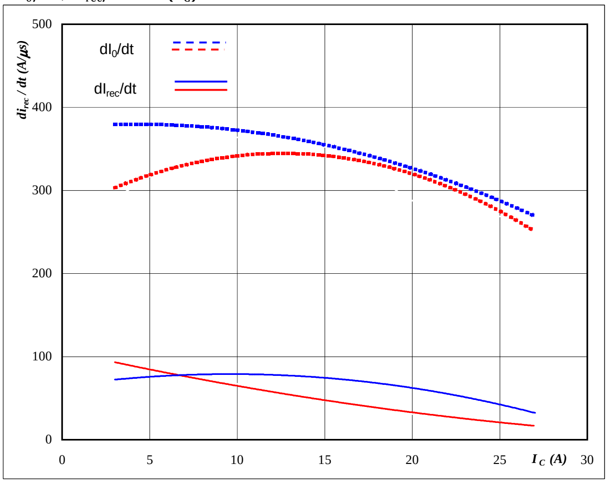
T_j =	25/150	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 17. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(I_C)$



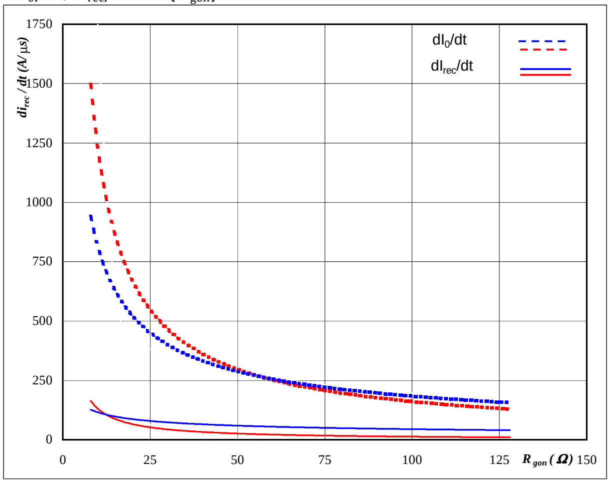
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	32	Ω

figure 18. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



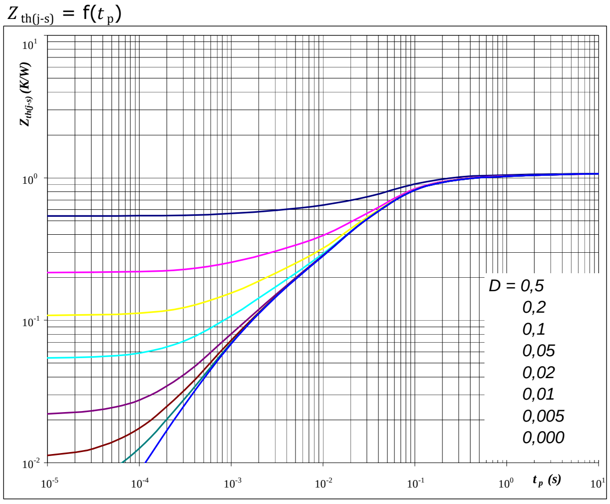
At

T_j =	25/150	°C
V_R =	600	V
I_F =	15	A
V_{GE} =	±15	V

figure 19. **IGBT**

IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

D =	t_p / T	
$R_{th(j-s)}$ =	1,08	K/W

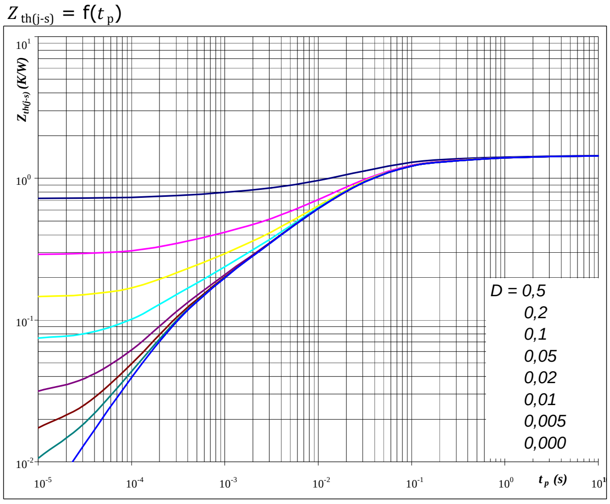
IGBT thermal model values

R (K/W)	Tau (s)
4,02E-02	8,05E+00
7,53E-02	6,86E-01
2,00E-01	1,22E-01
5,79E-01	4,09E-02
1,08E-01	7,96E-03
7,24E-02	1,22E-03
4,99E-03	5,90E-04

figure 20. **FWD**

FWD transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

D =	t_p / T	
$R_{th(j-s)}$ =	1,44	K/W

FWD thermal model values

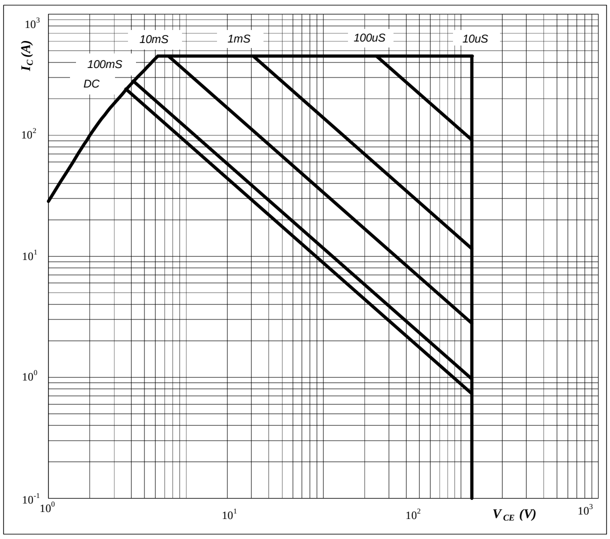
R (K/W)	Tau (s)
6,32E-02	2,64E+00
1,25E-01	3,53E-01
4,72E-01	5,08E-02
4,73E-01	1,56E-02
2,06E-01	2,93E-03
1,06E-01	3,09E-04

Inverter Switch / Brake Switch / Inverter Diode / Brake Diode

figure 25.	IGBT

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



At

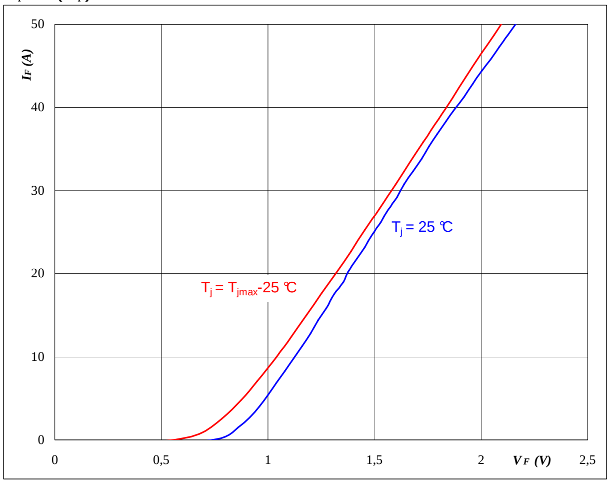
D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

Rectifier Diode

figure 1. **Diode**

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



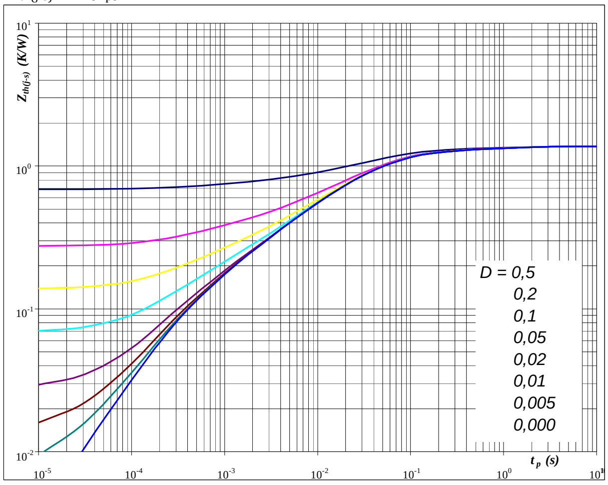
At

t_p = 250 µs

figure 2. **Diode**

Diode transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

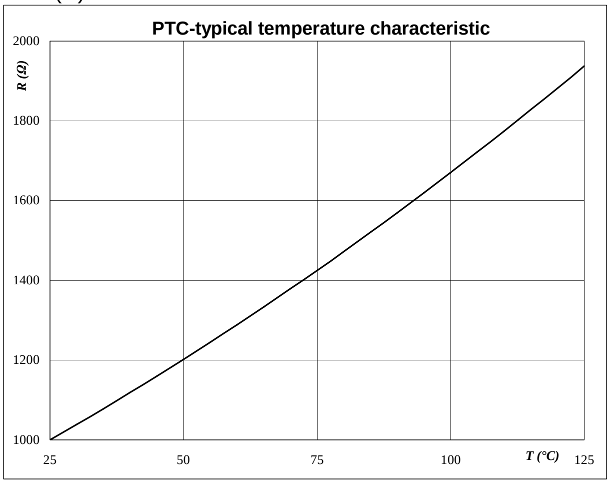
$D = t_p / T$

$R_{th(j-s)}$ = 1,37 K/W

Thermistor

figure 1.	Thermistor

Typical PTC characteristic
as a function of temperature
$R = f(T)$



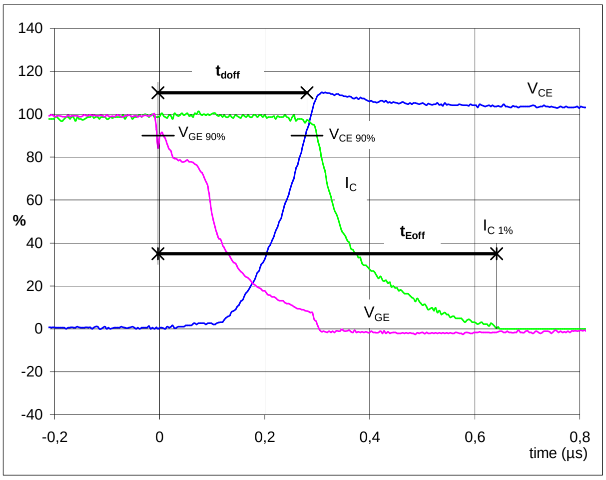
Switching Definitions

General conditions

T_j	=	150 °C
R_{gon}	=	32 Ω
R_{goff}	=	32 Ω

figure 1. **IGBT**

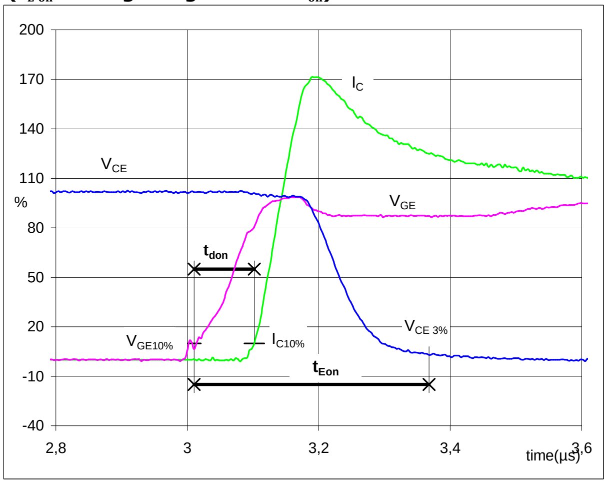
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff}
($t_{E off}$ = integrating time for E_{off})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	15	A
t_{doff} =	0,28	µs
$t_{E off}$ =	0,64	µs

figure 2. **IGBT**

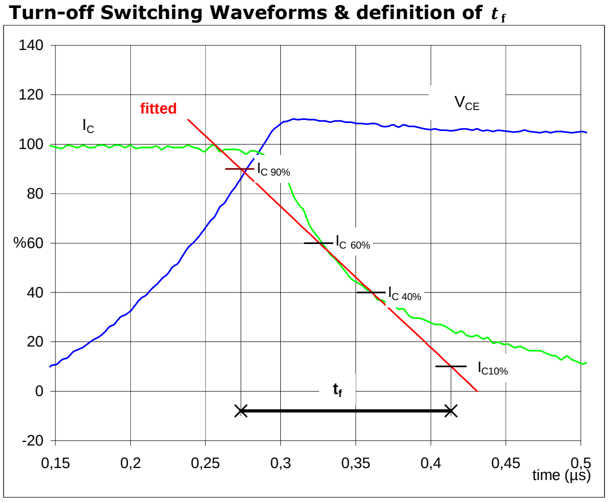
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon}
($t_{E on}$ = integrating time for E_{on})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	15	A
t_{don} =	0,10	µs
$t_{E on}$ =	0,36	µs

figure 3. **IGBT**

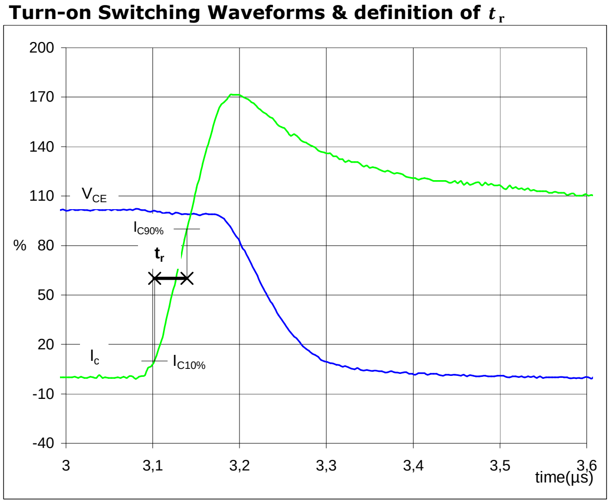
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	600	V
I_C (100%) =	15	A
t_f =	0,13	µs

figure 4. **IGBT**

Turn-on Switching Waveforms & definition of t_r

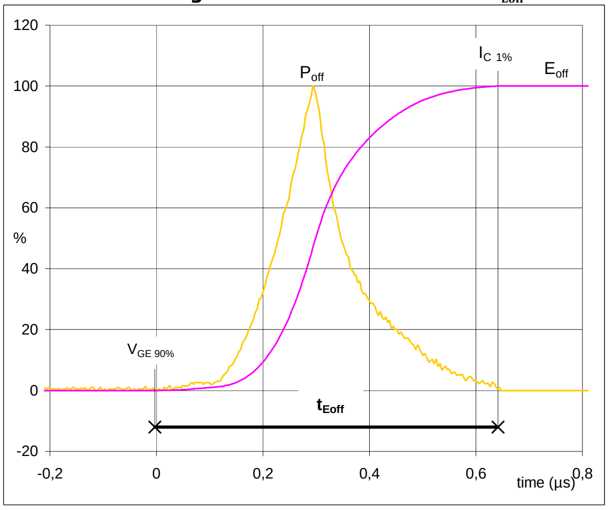


V_C (100%) =	600	V
I_C (100%) =	15	A
t_r =	0,04	µs

Switching Definitions

figure 5. **IGBT**

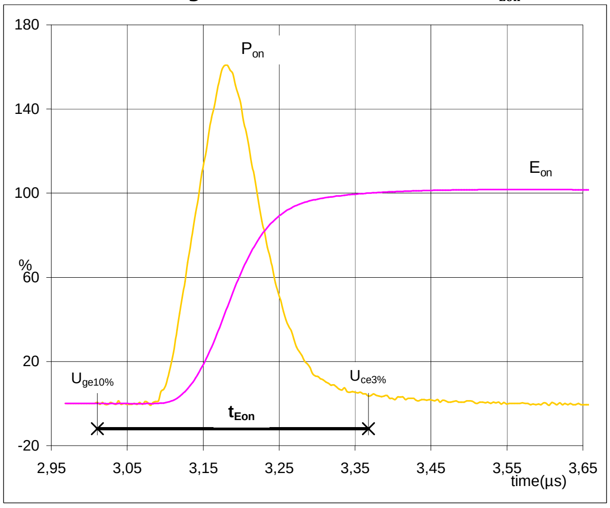
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) =	9,05	kW
E_{off} (100%) =	1,47	mJ
$t_{E\,off}$ =	0,64	µs

figure 6. **IGBT**

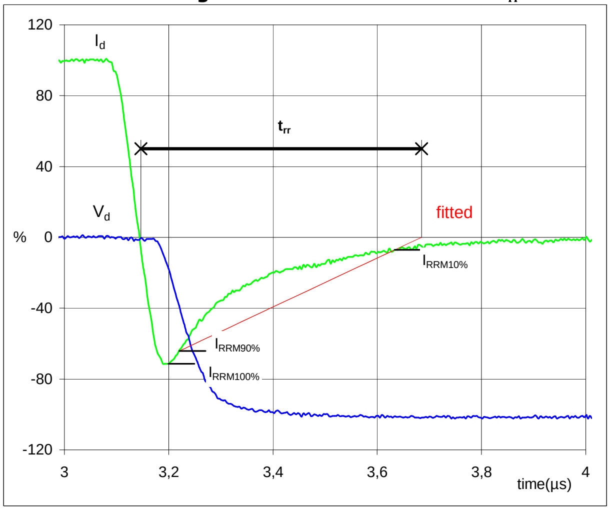
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) =	9,05	kW
E_{on} (100%) =	1,53	mJ
$t_{E\,on}$ =	0,36	µs

figure 7. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

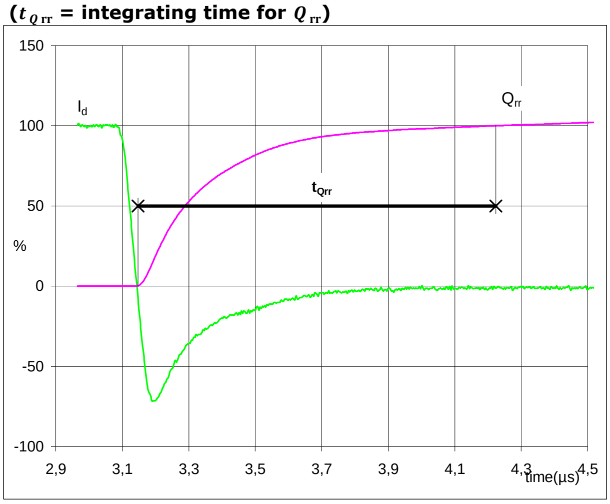


V_d (100%) =	600	V
I_d (100%) =	15	A
I_{RRM} (100%) =	-11	A
t_{rr} =	0,54	µs

Switching Definitions

figure 8.	**FWD**

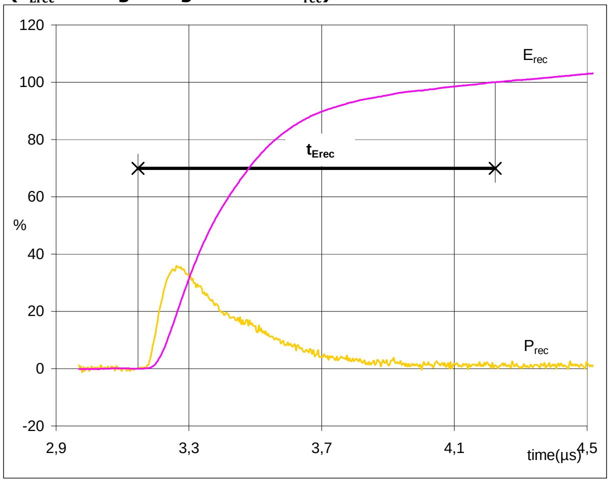
Turn-on Switching Waveforms & definition of t_{Qrr}
($t_{Q\,rr}$ = integrating time for Q_{rr})



I_d (100%) =	15	A
Q_{rr} (100%) =	2,33	µC
$t_{Q\,rr}$ =	1,08	µs

figure 9.	**FWD**

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec}= integrating time for E_{rec})



P_{rec} (100%) =	9,05	kW
E_{rec} (100%) =	0,97	mJ
$t_{E\,rec}$ =	1,08	µs

Ordering Code & Marking

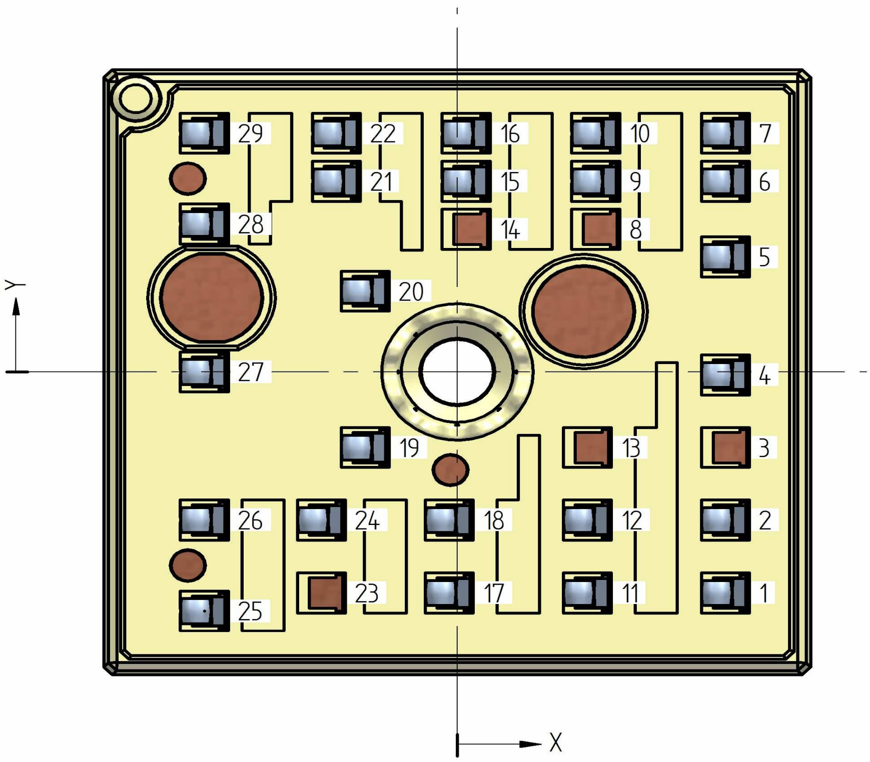
Version	Ordering Code
With std lid (6.5mm height) + no thermal grease	V23990-K200-A40-/0A/-PM
With thin lid (2.8mm height) + no thermal grease	V23990-K200-A40-/0B/-PM
With std lid (6.5mm height) + thermal grease (0,8 W/mK, P12, silicone-based)	V23990-K200-A40-/1A/-PM
With thin lid (2.8mm height) + thermal grease (0,8 W/mK, P12, silicone-based)	V23990-K200-A40-/1B/-PM
With std lid (6.5mm height) + thermal grease (2,5 W/mK, TG20032, silicone-free)	V23990-K200-A40-/4A/-PM
With thin lid (2.8mm height) + thermal grease (2,5 W/mK, TG20032, silicone-free)	V23990-K200-A40-/4B/-PM
With std lid (6.5mm height) + thermal grease (2,5 W/mK, HPTP, silicone-based)	V23990-K200-A40-/5A/-PM
With thin lid (2.8mm height) + thermal grease (2,5 W/mK, HPTP, silicone-based)	V23990-K200-A40-/5B/-PM

Text	VIN	Date code	Name&Ver	UL	Lot	Serial
	VIN	WWYY	NNNNNNVV	UL	LLLLL	SSSS
Datamatrix	Type&Ver	Lot number	Serial	Date code		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

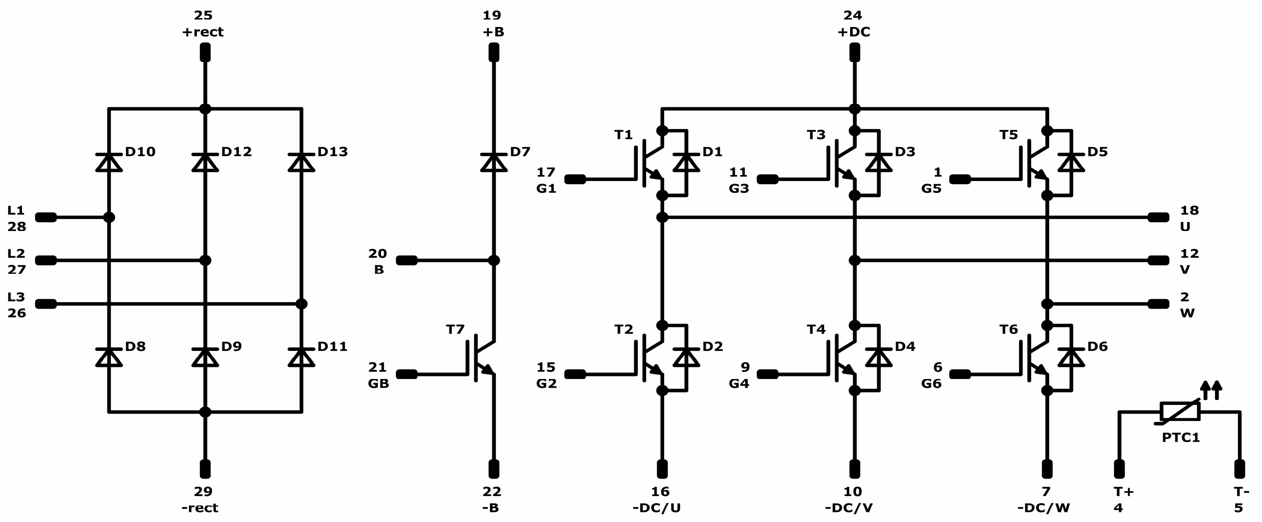
Pad table [mm]

Pad	X	Y	Function
1	15,93	-14,6	G5
2	15,93	-9,8	W
3	Not assembled		
4	15,93	-0,2	+T
5	15,93	7,62	-T
6	15,93	12,62	G6
7	15,93	15,8	-DC/W
8	Not assembled		
9	8,23	12,62	G4
10	8,23	15,8	-DC/V
11	7,73	-14,6	G3
12	7,73	-9,8	V
13	Not assembled		
14	Not assembled		
15	0,53	12,62	G2
16	0,53	15,8	-DC/U
17	-0,47	-14,6	G1
18	-0,47	-9,8	U
19	-5,47	-5	+B
20	-5,47	5,35	B
21	-7,17	12,62	GB
22	-7,17	15,8	-B
23	Not assembled		
24	-8,07	-9,8	+DC
25	-15,02	-15,8	+RECT
26	-15,02	-9,8	L3
27	-15,02	0	L2
28	-15,02	9,8	L1
29	-15,02	15,8	-RECT



Pad positions refers to center point. For more informations on pad design please see package data.

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
D8-D13	Rectifier	1600 V	25 A	Rectifier Diode	
T1-T6	IGBT	1200 V	15 A	Inverter Switch	
D1-D6	FWD	1200 V	15 A	Inverter Diode	
T7	IGBT	1200 V	15 A	Brake Switch	
D7	FWD	1200 V	15 A	Brake Diode	
PTC1	PTC			Thermistor	

Packaging instruction					
Standard packaging quantity (SPQ)	**120**	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for MiniSkiiP® 1 packages see vincotech.com website.

Package data
Package data for MiniSkiiP® 1 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
V23990-K200-A40-D7-14	12 Feb. 2018		